NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TVU0.5B** is Designed for Television Band IV & V Applications up to 860 MHz.

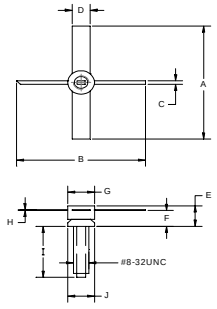
FEATURES:

- Common Emitter
- P_G = 12 dB at 0.5 W/860 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	2.0 A
V_{CBO}	45 V
V_{CEO}	25 V
V_{EBO}	3.5 V
P_{DISS}	31.8 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	33 °C/W

PACKAGE STYLE .205 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.976 / 24.800	1.000 / 25.4000
B	.976 / 24.800	1.000 / 25.4000
C	.028 / 0.700	.031 / 0.800
D	.138 / 3.500	
E	.161 / 4.100	.196 / 5.000
F	.098 / 2.500	.110 / 2.800
G	.200 / 5.100	.208 / 5.300
H	.004 / 0.100	.006 / 0.150
I	.425 / 10.800	.465 / 11.800
J	.200 / 5.100	2.05 / 5.200

ORDER CODE: ASI10642

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 1.0 mA	45			V
BV_{CE}	I_C = 20 mA	24			V
BV_{EBO}	I_E = 0.25 mA	3.5			V
I_{CBO}	V_{CB} = 28 V			0.45	mA
h_{FE}	V_{CE} = 5.0 V I_C = 100 mA	15		120	---
P_G	V_{CE} = 20 V I_C = 150 mA f = 860 MHz	12			dB
IMD_1	P_{OUT} = 0.5 W	-58			dBc